

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)		ATTY DOCKET NO. 35.C12475 Div. I		APPLICATION NO. Div. of 08/999,132		JC531 U.S. PAT. 09/638398	
APPLICANT KATSUMI NAKAGAWA ET AL.		FILING DATE Herewith		GROUP 2812			

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
SM	4,778,478	10/18/88	Barnett	437	5		
	5,536,361	7/16/96	Kondo et al.	156	630.1		
	4,774,194	9/27/88	Hokuyou	437	5		
	4,058,418	11/15/77	Lindmayer	148	175		
	5,856,229	1/5/99	Sakaguchi et al.	438	406		
	5,966,620	10/12/99	Sakaguchi et al.	438	455		
	5,492,859	2/20/96	Sakaguchi et al.	437	86		
SM	5,840,616	11/24/98	Sakaguchi et al.	438	459		


FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT	
SM	7-302889	11/14/95	Japan			abstract	
	8-97389	4/12/96	Japan			abstract	
	8-213645	8/20/96	Japan			abstract	
	5-211128	8/20/93	Japan			abstract	
SM	6-191987	7/12/94	Japan			abstract	

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)	
SM	H. Baumgart, et al., "Dielectric Isolation Using Porous Silicon", Mat. Res. Soc. Symp. Proc., vol. 33, pp. 63-68 (1994).
P	Nikkei Microdevices, pp. 76-77 (1994).
P	P. Schmuki, et al., "Initiation and Formation of Porous GaAs", J. Electrochem. Soc., vol. 143, no. 10, pp. 3316-3322 (1996).
P	T. Unagami, "Formation Mechanism of Porous Silicon Layer by Anodization in HF Solution", J. Electrochem. Soc., vol. 127, no. 2, pp. 476-483 (1980).
P	R.P. Holmstrom, et al., "Composite dielectric isolation by highly selective and self-stopping formation of oxidized porous silicon", Appl. Phys. Lett., vol. 42, no. 4, pp. 386-388 (1983).
SM	A.G. Mills, et al., "Peelable Film Technology for Solar Cells", 11 th IEEE Photovoltaic Spec. Conf., Scottsdale, Arizona, pp. 338-341 (1975).

EXAMINER		DATE CONSIDERED	12/29/00
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>San</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	5,277,748	1/11/94	Sakaguchi et al.	156	630	 08/15/00 09/638398	
	5,811,348	9/22/98	Matsushita et al.	438	455		
	5,391,257	2/21/95	Sullivan et al.	156	630		
	5,371,037	12/6/94	Yonehara	437	86		
	4,816,420	3/28/89	Bozler et al.	437	2		
<i>San</i>	5,374,564	12/20/94	Bruel	437	24		

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT	
<i>San</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	5-21338	1/29/93	Japan	—	—	abstract	
	0 688 048	12/20/95	EP	—	—		
	0 272 636	06/29/88	EP	—	—		
	0 703 609	3/27/96	EP	—	—	abstract	
	81/02948	10/15/81	PCT	—	—		
<i>San</i>	6-45622	2/18/94	Japan	—	—	abstract	

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)		

EXAMINER <i>San</i>	DATE CONSIDERED <i>12/29/00</i>
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